The e ect of uniaxial pressure on the magnetic anom alies of the heavy-ferm ion metam agnet C eR u₂S i₂

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The e ect of uniaxial pressure (P_u) on the magnetic susceptibility (), magnetization (M), and magnetoresistance (MR) of the heavy-ferm ion metamagnet CeRu₂Si₂ has been investigated. For the magnetic eld along the tetragonal caxis, it is found that characteristic physical quantities, i.e., the temperature of the susceptibility maximum (T_{max}), the pagamagnetic W eiss temperature ($_p$), 1= at 2 K, and the magnetic eld of the metamagnetic anomaly (H_M), scale approximately linearly with P_u , indicating that all the quantities are related to the same energy scale, probably of the K ondo temperature. The increase (decrease) of the quantities for P_u k caxis (P_u k a axis) can be attributed to a decrease (increase) in the nearest Ce-R u distance. Consistently in MR and , we observed a sign that the anisotropic nature of the hybridization, which is believed to play an in portant role in the metam agnetic anomaly, can be controlled by applying the uniaxial pressure.

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I. IN TRODUCTION

The compound, CeRu₂Si₂, crystallizing in the tetragonal ThC r₂Si₂-type structure, is one of the most intensively studied and best characterized systems among the heavy-ferm ion compounds.¹ The reason is that apart from a large electronic specic-heat coe -360 mJ/molK² in zero eld,^{2,3} there is an cient abrupt nonlinear increase of magnetization, the so called metamagnetic anomaly (MA) from a paramagnetic ground state, around an external magnetic eld of 80 kO e (Ref. 1) applied only along the caxis Н_М of the tetragonal structure below 15 K.Not only the magnetization process but also many other physical properties have been reported to be anom alous in this eld region around H M .3,4,5,6

The origin of the anom aly is still a matter of debate, despite intensive investigations. The de Haas-van Alphen e ect studies have shown that both the Ferm i surface and the elective mass change considerably around ${\rm H}_{\,\rm M}$, suggesting a change of 4f-electron character from it inerance in the low-eld state to localization in the high-eld state.4 In contrast, low-tem perature magnetization m easurem ents⁵ suggest that the low - eld state is continuously connected to the high-eld state across H_{M} . M oreover, a peak observed in the Hall resistivity at $H = H_M$ disappears on approaching T = 0, suggesting no abrupt change in the Fermi surface.6 Reports of hydrostatic pressure experim ents^{7,8} reveal that the volum e reduction enhances the characteristic energy of the quasiparticle system and leads to a drastic shift of H_{M} to higher elds. From this large e ect of pressure a very large electronic G runeisen param eter 185 M bar¹ has been inferred. The anisotropic hybridization between 4f and conduction electrons leading to an anom alous peak in the quasiparticle density-of-states (DOS) is argued to play an important role in the MA; the MA appears

when the peak crosses the Ferm i level at high m agnetic eks.^{3,9} However, no direct evidence of the anisotropic hybridization e ect can be obtained from hydrostatic pressure experiments. The uniaxial-pressure experiment has the potential for providing useful information on anisotropic hybridization. In view of these reasons, we have investigated the e ect of uniaxial pressure in $C \in Ru_2Si_2$ with m agnetic and transport experiments.

II. EXPERIMENT

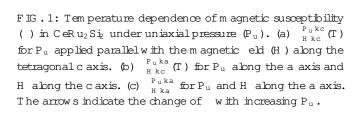
Single crystals of CeRu₂Si₂ were grown by the Czochralski pulling method in a tetra-arc furnace with an argon atmosphere. The single crystalline nature was con med by back-re ection-Laue techniques. The high quality of the single crystal was inferred from the residual resistivity ratio 110. Electrical resistivity and magnetoresistance were measured by the standard dc four probe method using a computer-controlled current source and nanovoltm eter (182 K eithley), using a top-loading ³H e cryostat equipped with a 160 kO e superconducting magnet (Oxford Instruments Co., Ltd.). The electrical contacts of Ag current leads were a xed to the sample by indium soldering. Au wires of 80-m were spotwelded to the sample as voltage leads. Uniaxial pressures were generated by using a piston-cylinder-type CuBe pressure cell for transport experiments, recently designed and constructed by us¹⁰, so as to suit the above cryostat. Single-crystal samples (typical dimensions:

 $0.7 \times 1 \times 2 \text{ mm}^3$) were sandwiched between two disc-shaped ZrO_2 plates, which provided the electrical isolation. A Nit on tape of 0.08 -mm thickness was placed between the sample and ZrO_2 plates in order to prevent the breaking of the sample due to its surface roughness under pressure, if any. Uniaxial pressures were

applied on a ZrO₂ ball, placed inside a ring-shaped guide on the ZrO₂ plate above the sam ple, which prevented any rotation of the sample under pressure. Uniaxial pressures produced on the sample at low temperatures were calibrated by measuring the superconducting transition temperature of Sn placed in the cell by an induction m ethod. M agnetic properties were m easured by a commercial superconducting quantum interference device (SQUID) magnetometer. Uniaxial pressures parallel to the magnetic elds were generated by using a modi ed version of the SQUD-pressure cell reported by Uwatoko et al.¹¹ Uniaxial pressures produced on the rectangular shaped single crystal ($1.5 \times 1.5 \times 2$ mm³) at low tem peratures were calibrated by measuring the Meissner e ect of a small piece of Pb, placed in the pressure cell. The known pressure dependences of the superconducting transition temperature of Sn (Ref. 12) (for transport measurements) and Pb (Ref. 13) were used for these purposes. Uniaxial pressures perpendicular to the magnetic elds were generated by a uniaxial-pressure cell recently designed and constructed by us¹⁰. In this case, the uniaxial pressures were determ ined at room temperature by the absolute value of force applied on the sam ple. The total magnetization of the sam ple and the uniaxial-pressure cell were m easured by SQUD magnetometer and the magnetization of the uniaxial-pressure cell, though sm all (1 10%), were subtracted from the total magnetization to obtain the precise value of the sam ple m agnetization.

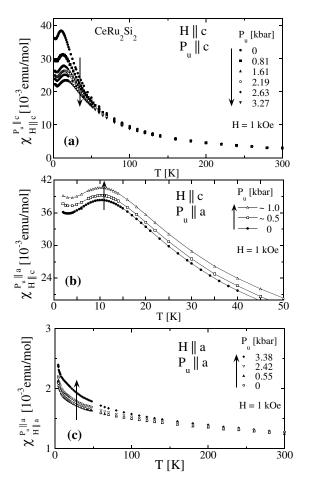
III. EXPERIMENTAL RESULTS

Figure 1 shows the e ect of uniaxial pressure on the tem perature dependence of magnetic susceptibility (T) in CeRu₂Si₂; Fig. 1(a) is for P_u k H k c axis, Fig. 1(b) is for P_u k a and H k c axis, and Fig. 1(c) is for P_u k H k a axis. At am bient pressure, the m agnetic susceptibility is strongly anisotropic depending on whether H is applied parallel or perpendicular to the tetragonal caxis. _{H kc} (T) obeys the Curie-W eiss law above 70 K and then shows a maximum at a temperature $T_{m ax}$ ' 10 K, which is considered to provide a measure of the K ondo tem perature $T_{\rm K}$. $_{\rm H~ka}$ (T) also follow s the Curie-W eiss law above 100 K, and it exhibits much sm aller values than $_{\rm H~kc}$ (T), without showing any m axin um . The anisotropy ratio $_{\rm H~kc}$ (T)/ $_{\rm H~ka}$ (T) increases largely with decreasing temperatures. These behaviors at am bient pressure are consistent with those reported before⁷. W hen the uniaxial pressure of P_u k c axis is applied, $P_{u kc}$ for H k c-axis is largely suppressed at low tem peratures with increasing P_u , though the e ect of P_u is small at higher tem perature (100 K). T_{m ax} shifts to higher tem peratures with increasing P_u , i.e., T_{max} / 16.5 K at P_u ' 3.27 kbar. The pressure dependence is alm ost similar to that under hydrostatic pressure (P_h) repoted in Refs. 7 and 8. By contrast, when P_u is applied per-



pendicular to the magnetic eld, i.e., P_u k a axis, $P_u^{P_u ka}_{H kc}$ at low temperatures is enhanced and $T_{m ax}$ is slightly suppressed [see F ig. 1 (b)]. On the other hand for H k a axis, $P_u^{P_u ka}_{H ka}$ slightly increases at low temperatures with P_u k a axis [see F ig. 1 (c)]. This increase of $P_u^{P_u ka}_{H ka}$ is also in contrast to the decrease of $P_h^{P_u}_{H ka}$ under hydrostatic pressure⁷. In the case of P_u k c axis, $P_u^{P_u kc}_{H ka}$ weakly enhances at low temperatures with P_u (not shown); it is di cult to separate accurately the background contribution from the pressure cell which is com parable to the sam ple m agnetization for H k a axis.

Figure 2 shows the e ect of uniaxial pressure on the m agnetic- eld dependence of isotherm al (at 2 K) m agnetization M (H) in C eR $u_2 Si_2$. The am bient pressure data are consistent with those reported before⁷. For H k c axis, a positive curvature of M $_{\rm H~kc}^{\rm P_u~kc}$ (H) is observed as a



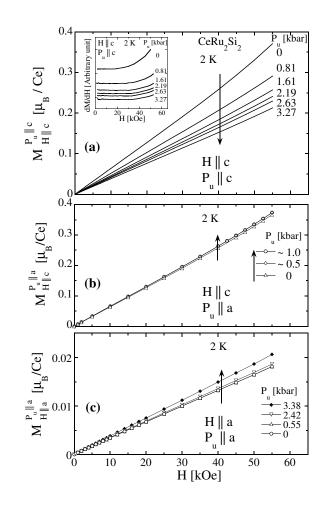


FIG. 2: Magnetic-eld dependence of isotherm al magnetization M (H) in CeRu₂Si₂ under uniaxial pressure at 2 K. (a) M $_{H \ kc}^{P_u \ kc}$ (H) for P_u applied parallel with the magnetic eld along the tetragonal c axis. (b) M $_{H \ kc}^{P_u \ ka}$ (H) for P_u along the a axis and H along the c axis. (c) M $_{H \ ka}^{P_u \ ka}$ (H) for P_u and H along the a axis. The arrows indicate the change of M with increasing P_u. The solid lines are guides to the eyes.

precursor to the m etam agnetic anom aly at H_M ′ 80 kO e at am bient pressure. Under P_u k c axis, M $_{\rm H~kc}^{\rm P_u~kc}$ up to 55 kO e drastically decreases [see Fig. 2(a)] and the curvature $(M_{\rm H~kc}^{\rm P_u~kc}=0)$ at 55 kO e is also largely suppressed with increasing P_u as shown in the inset of Fig. 2(a). These facts indicate a shift of the m etam agnetic anom aly to higher m agnetic elds by P_u k c axis; actually, this is con m ed by the m agnetoresistance m easurem ent (see Fig. 3). This e ect of P_u k c axis on the isotherm alm agnetization M $_{\rm H~kc}^{\rm P_h}$ (H) reported in Ref. 7, where M $_{\rm H~kc}^{\rm P_h}$ and $(M_{\rm H~kc}^{\rm P_h}=0)$ reported in Ref. 7, where M $_{\rm H~kc}^{\rm P_h}$ and $(M_{\rm H~kc}^{\rm P_h}=0)$ and the $(M_{\rm H~kc}^{\rm P_u~ka}=0)$ H at 55 kO e is also weakly enhanced. On the other hand for H k a axis, P_u k a axis enhances $M_{H ka}^{P ka}$ [see Fig. 2(c)]. This increase of $M_{H ka}^{P_u ka}$ is in sharp contrast to the decrease of $M_{H ka}^{P_h}$ under hydrostatic pressure⁷.

In order to see the e ect of uniaxial pressure on

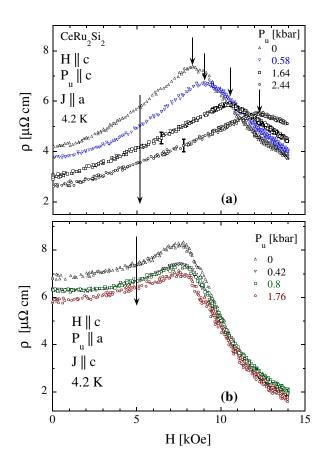


FIG.3: M agnetoresistance (M R) in C eR $u_2 S i_2$ at 4.2 K under uniaxial pressure P_u (a) for P_u k c axis (0 P_u 2.44 kbar) and transverse geometry (H k c axis, J k a axis). The short arrows indicate the magnetic elds H_M where the maximum in (H) occurs, rejecting the metam agnetic anomaly. The error bars are put in the vertical axis after smoothing the scattered data points at higher pressures due to deterioration of the spotweld of the voltage leads. (b) for P_u k a axis (0

 $P_{\rm u}$ 1.76 kbar) and longitudinal geometry (H kJ kc axis). The long arrows indicate the decrease of below H_M with increasing $P_{\rm u}$ in both gures.

the M A, we have m easured the m agnetoresistance (M R) up to 140 kO e under P_u . Figure 3(a) shows the e ect of P_u k c axis on the m agnetic eld dependence of the transverse m agnetoresistance, i.e., H along the c axis and the current J along the a axis. The data for P_u 0 kbar are in close agreem ent with that reported in Ref. 8. The resistivity increases with m agnetic elds and then shows a m axim um or peak at H m ax '83 kO e. The M A m anifests

itself in this peak at H $_{\rm m\,ax}$ (\rm H $_{\rm M}$). W ith increasing P $_{\rm u}$, the resistivity below H_M decreases and the peak shifts to higher H as marked by vertical arrows. These behaviors are sim ilar to those under hydrostatic pressure reported in Ref. 8, though there are small quantitative di erences. The most signi cant di erences are that the absolute value of at the peak (at H_M) decreases and the shape of the peak broadens with increasing P_u k c-axis, while these remain alm ost unchanged for all values of P_h . These behaviors under P_h have been ascribed to the im plication that the quasiparticle DOS always reaches the sam e critical value at H $_{\rm M}$ 8 . This conclusion was made by taking into account the following facts: H_M depends on pressure but it depends only slightly on tem perature. At all values of P_h , the at $H = H_M$ of the corresponding P_h shows alm ost the same tem perature dependence. Therefore, the slope of each (T) curve of $H = H_M$, which gives an estimation about the DOS at $H = H_M$, remains unchanged with P_h^8 . Based on the same model, in the present case under P_u k c axis, the decrease and broadening of the peak at H_M may indicate a change of the quasiparticle DOS near the metam agnetic anom aly at H_M with increasing P_u k c axis. However, measurem ents at low tem peratures are necessary in order to reach a decisive conclusion.

Figure 3(b) shows the e ect of P_u k a axis on the magnetic eld dependence of longitudinalm agnetoresistance, i.e., H along caxis and J along the a axis. The application of P_u k a axis is very risky, since large cracks easily develop into the sam ples. Som e sam ples were com pletely separated into pieces in the c plane under pressure, m aking the measurement impossible several times. The ambient pressure (\mathbb{P}_{u}) 0) data cannot be compared with that of Ref. 8, since there is no data for this geometry, how ever, the data are consistent in nature to the reported longitudinalMR at lower tem peratures by K am be et al.⁶. The data for P_{u} 0 and 0.8 kbar have been taken on the same sample piece, but for P_u 0.4 and 1.76 kbar the data have been taken on two di erent sam ple pieces, although all the pieces were cut from the adjacent part of the same crystal. The results shown in Fig. 3 (b) indicate that the sample dependence is minor at least for these three pieces. With increasing P_u k a axis, the resistivity decreases for all H , though the change in above H_M is smaller than that below H_M . The magnetoresistance peak at H_{M} (80 kO e at am bient pressure), manifesting the m etam agnetic anom aly, changes only slightly with increasing P_u . There is a slight decreasing tendency of H $_M$ [see Fig. 4 (c)] with increasing P_u , although it is dicult to determ ine accurately the rate $H_M = P_u$ due to its extrem ely sm all change relative to the experim ental accuracy.

Figure 4 (a) shows the dependence of $T_{m\ ax}\ in \ _{H\ kc}$ (T) on P_u along with that on P_h reported by Voiron et al.⁷. $T_{m\ ax}$ is enhanced with $P_u\ k\ c\ ax$ is as $dT_{m\ ax}=dP_u\ '\ 1.85$

0.1 K /kbar which is close to the rate $dT_{m ax}=dP_{h}$ ' 2.5 K /kbar for the P_{h} reported in Refs. 7 and 8. The absolute value of the param agnetic W eiss tem perature _____, de-

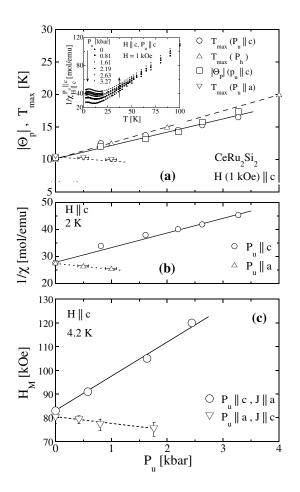


FIG. 4: (a) Uniaxial pressure dependence of $T_{m ax}$ in $\frac{P_u kc}{H kc}$ and the absolute value of the param agnetic W eiss tem perature p, estim ated from the linear region of the inverse $\frac{P_u kc}{H kc}$ plot below 100 K shown in the inset; the evolution of $T_{m ax}$ under P_h reproduced from the report by Voiron et al. (R ef. 7) is also ploted at the same time. (b) Uniaxial-pressure dependence of the inverse $\frac{P_u kc}{H kc}$ and $\frac{P_u ka}{H kc}$ at 2 K. (c) Uniaxial pressure dependence of H_k in the transverse (H k c axis, J k a axis) m agnetoresistance under P_u k c-axis and longitudinal (H k J k c axis) m agnetoresistance under P_u k a axis in C eR u₂Si₂. The solid and broken lines are guides to eyes.

term ined from the linear region of the inverse of $\frac{P_u kc}{H kc}$ (T) plot (below 100 K) shown in the inset of Figure 4 (a), is also found to increase with P_u k c axis as shown in the same gure. The negative sign of $_p$ can be attributed to K ondo correlations. On the other hand, T_{max} is suppressed by P_u k a axis. Fig. 4 (b) shows the P_u dependence of 1/ $_{H kc}$ at T = 2 K, which is enhanced and suppressed by P_u k c axis and P_u k a axis, respectively. Note that the low-temperature value of 1 is proportional to the K ondo temperature T_K in the Fermi-Hiquid regime. Figure 4 (c) shows the P_u dependence of H_M in M R. H_M strongly increases by P_u k c axis as $H_M = P_u$ 17 2 kO e/kbarwhich is close to the rate 20 kO e/kbar under P_h^8 , while H_M slightly decreases by P_u k a axis.

M ignot et al.⁸ have shown that the hydrostatic pressure dependence of T_{max} , $T_{1,0}^{1}$, and H_{M} show a scaling behavior. A similar plot has been made as a function of P_u , where all the quantities T_{max} , p, $T_{,0}^{1}$, and H_M are norm alized by their am bient pressure values as shown in Fig. 5. T_{max} under P_h norm alized by the ambient pressure value is also plotted for com parison. It is clear that all the quantities scale roughly falling on the same lines. This fact indicates, similar to the case of hydrostatic pressure, an existence of a single energy parameter that determ ines the low tem perature properties controlled by P_u. Considering that both the low-tem perature value of ${}_{\mathrm{T}}^{1},{}_{0}$ in the Ferm i-liquid regime and ${}_{\mathrm{p}}$ are proportional to the K ondo tem perature $T_{\rm K}$, the observed scaling strongly indicates that both $T_{m ax}$ and H_{M} are also related to the K ondo e ect. The strong increase (weak decrease) of all the quantities indicates the strong enhancement (the weak suppression) of hybridization between conduction and f electrons under P_{ij} k c axis (P_{ij} k a axis). In other words, T_K is strongly increased by P_u k c axis, while it is decreased by P_u k a axis.

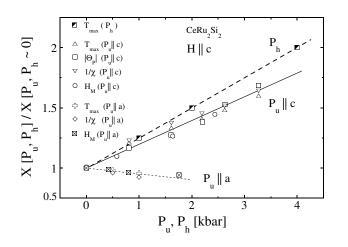


FIG.5: $T_{m ax}$, p, $T_{r 0}^{1}$, and H_{M} normalized by the ambient pressure value of each parameter as a function of P_{u} . Solid lines are drawn to show that all the normalized parameters (X) for the same uniaxial-pressure geometry fall roughly on the same line. $T_{m ax}$ under P_{h} , reported in Ref. 7 normalized by the ambient pressure value is also ploted at the same time. The solid and broken lines are guides to the eyes.

IV. DISCUSSIONS

In the previous section, we have shown that the effect of uniaxial pressures on the transport and m agnetic properties is quite anisotropic. E specially, a qualitatively opposite e ect on T_K is observed between P_u k a axis and P_u k c axis con gurations. In order to understand this, we estimate the movement of the surrounding ions

relative to the Ce ions due to the uniaxial pressures, taking into account the elastic properties reported to date.

The elastic constants of $C \in Ru_2Si_2$ at 300 K have been reported by Weber¹⁴, i.e., C_{11} ' 2.145, C_{12} ' 0.67, C $_{\rm 33}$ ' 1.215, and C $_{\rm 13}$ ' 0.806 M bar. W e use these values since the low temperature values are not complete; no data are available at low temperatures for C_{12} in Ref. 14. Note that the temperature dependence of these quantities does not qualitatively a ect our consequence shown below. Using these values, the linear compressibilities along the principal crystalline directions are then calculated as a $[a=P_u]=a' 0.63 M bar^1$ $[c=P_u]=c'$ 1.33 M bar¹ for the a axis and _c and c axis, respectively. Three Poisson ratios are also calculated. Under ${\tt P}_{\rm u}\,$ k a axis, the Poisson ratio along the caxis is $c^{P_u ka}$ / 0.608, while that along another a axis is $a^{P_u ka}$ / 0.084. On the other hand under $P_u kc$ axis, the Poisson ratio is $a^{P_u kc}$ / 0.286. The values are quite an isotropic, i.e., for P_u along the a axis, the elongation along the c axis is more than seven times larger than that along the other a axis.

It is believed that the hybridization between f states and conduction electrons in $C \in Ru_2Si_2$ is mainly governed by d-f hybridization¹⁵. The band-structure calculation¹⁶ indicates that there are ve bands crossing the Ferm i level (four hole sheets and one electron sheet), and they consist dominantly of the Ce 4f and the Ru 4d components. A ctually, the nearest atom from Ce ions is Ru, suggesting strong hybridization between 4f and 4d electrons. Using the same lattice constants and atom ic positions used in Ref. 16, the distances between the nearest neighbor Ce-Ru are calculated as a function of uniaxial pressure. The results are shown in Fig. 6. For the cases of applied uniaxial pressure along the c-axis and hydrostatic pressure, Ce-Ru distance d_{Ce Ru} (= 3.224 A at am bient pressure) decreases. On the other hand for the uniaxial pressure along the a axis, the crystal symmetry decreases from tetragonal to orthorhom bic and two unequivalent d_{CeRu} appear, however, the average value of d_{Ce} _{Ru} weakly increases. In the form er case, decreasing d_{Ce}_{Ru} should cause an increase of the d-f exchange interaction J_{df} , and also an increase of T_K , which depends on J_{df} essentially as / $\exp[1=J_{df}N(E_F)]$, where N(E_F) represents the density of states on the Fermi energy and is less sensitive to pressure than J_{df} . On the contrary, the uniaxial pressure along the a axis should decrease J_{df} and hence $T_{\mbox{\scriptsize K}}$. These expectations are qualitatively consistent with the present observation. Especially, sim ilar behavior observed for the cases of P_u k c axis and hydrostatic pressure experim ents are naturally explained as a consequence of the sim ilar pressure dependencies of d_{Ce Ru}.

The large anisotropy in the magnetic susceptibility in $CeRu_2Si_2$ is ascribed to the crystalline electric eld (CEF) e ect. At ambient pressure, the anisotropy

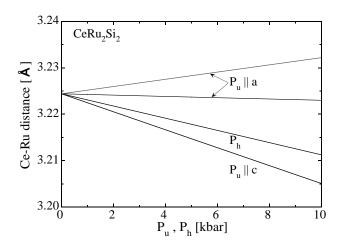


FIG.6:E stim ated change of C = R u distance in $C = R u_2 S i_2$ with uniaxial and hydrostatic pressure using the values of elastic constants (R ef. 14). The solid lines are guides to the eyes.

Hkc/Hkap. 15 at 4.2 K suggests the ground state is (1 a²)j <u>3</u>i,a 0:96.⁹ The maximum aj anisotropy in the magnetic susceptibility is expected for a CEF ground state of pure j $\frac{5}{2}$ i. _{H kc} is largely suppressed, while Hka is slightly enhanced by Pu k c axis. Therefore, the anisotropy $_{H \ kc} = _{H \ ka}$ decreases with increasing ${\tt P}_u$ k c axis. This may relect a change of the CEF ground state, i.e., an increase of the j $\frac{3}{2}$ i component in the ground state by P_u k c axis. For the Ce^{3+} ion, the charge distribution of j $\frac{3}{2}i$ is dum bbell shaped with its elongation along the c-axis¹⁷. M oreover in the CeRu₂Si₂ crystal unit cell, the Ru atom is located at $(0; \frac{1}{2}; \frac{1}{4})$ with respect to the Ce ion.¹⁶ Therefore, besides the decrease of Ce-Ru distance, an increase of the j $\frac{3}{2}$ i component also consistently favors the strong enhancem ent of Ce-Ru hybridization by P_u k c axis. It is argued that there is an anom alous peak structure in the partial density of the hybridized-band state (the DOS) due to anisotropic hybridization between 4f and conduction electrons in the case where the lowest CEF level is $j = \frac{5}{2}i^{3,9}$. In this case, the anisotropic hybridization has an angular dependence characterized by $(1 \hat{k}_z^2)^2$. The dimensional susceptibility diverges when the peak in the DOS crosses the Ferm i level giving rise to the m etam agnetic anom aly at H $_{\rm M}\,$. A s discussed

in the previous section comparing the transverse MR under P_u k c axis with the reported MR behavior under hydrostatic pressure, the decrease and broadening of the peak at $H_{m ax}$ may suggest a change of DOS with P_u k c axis. A possible change of the CEF ground state, i.e., an increase of the j $\frac{3}{2}i$ component by P_u k c axis may cause a decrease and broadening of the anom alous peak in the DOS near the Ferm i level predicted for anisotropic hybridization. It may be noted that for a pure j $\frac{3}{2}i$ ground state the DOS near the Ferm i level has a nite value rather than a peak as shown in the case of the K ondo insulator CeN isn^{9,18}. In order to determ ine the quantitative change or broadening of the DOS, measurem ents of the eld dependence of speci c heat under uniaxial pressure are needed.

V. CONCLUSION

We have found that the uniaxial pressure has an anisotropic e ect on the magnetic and transport properties in the heavy-ferm ion m etam agnet $C \in Ru_2Si_2$ with a direct in uence on the hybridization. The characteristic parameters T_{max} , p, T'_{0} , and H_{M} roughly scale as the uniaxial pressure is varied, leading to a single-energy-scale picture, namely, the variation of T_K . The results suggest that T_K (or d-f hybridization) is strongly enhanced for the pressure along the c axis due to the decrease of the nearest Ce-Ru distance, while T_K is weakly suppressed for the pressure along the a axis due to the increase of Ce-Ru distance. The decrease of the anisotropy of magnetic susceptibility and the decrease and broadening of the magnetoresistance peak at the metam agnetic anom aly indicate a controlling of the anisotropic hybridization by uniaxial pressure.

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